



DMN10H120SE-13 Information

For Reference Only

Part Number DMN10H120SE-13 Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 3.6A SOT223

TO-261-4, TO-261AA **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









DMN10H120SE-13 Specifications

Manufacturer Part Number DMN10H120SE-13 Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-261-4, TO-261AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 3.6A (Ta) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 10nC @ 10V Input Capacitance (Ciss) (Max) @ Vds \$49pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 110 mOhm @ 3.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA		
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Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 3.6A (Ta) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 10nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 549pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 110 mOhm @ 3.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C3.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs10nC @ 10VInput Capacitance (Ciss) (Max) @ Vds549pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs110 mOhm @ 3.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Package	TO-261-4, TO-261AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C3.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs10nC @ 10VInput Capacitance (Ciss) (Max) @ Vds549pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs110 mOhm @ 3.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C3.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs10nC @ 10VInput Capacitance (Ciss) (Max) @ Vds549pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs110 mOhm @ 3.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 3.3A, 10V Operating Temperature Supplier Device Package Package / Case 3.6A (Ta) 5.50 C 10V Supplier Device 10V Supplier Device Package SOT-223 TO-261-4, TO-261AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs10nC @ 10VInput Capacitance (Ciss) (Max) @ Vds549pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs110 mOhm @ 3.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Input Capacitance - Surface Mount Supplier Device Package Package / Case 10nC @ 10V 110nC @ 10V 140 140 140 140 140 140 154 159 160 160 160 160 160 160 160 16	Current - Continuous Drain (Id) @ 25°C	3.6A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 549pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 3.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Drive Voltage (Max Rds On, Min Rds On)	6V, 10V
Input Capacitance (Ciss) (Max) @ Vds 549pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 3.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs110 mOhm @ 3.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Gate Charge (Qg) (Max) @ Vgs	10nC @ 10V
FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 110 mOhm @ 3.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Input Capacitance (Ciss) (Max) @ Vds	549pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 3.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs110 mOhm @ 3.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Power Dissipation (Max)	1.3W (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Rds On (Max) @ Id, Vgs	110 mOhm @ 3.3A, 10V
Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-261-4, TO-261AA	Mounting Type	Surface Mount
	Supplier Device Package	SOT-223
Report errors?	Package / Case	TO-261-4, TO-261AA
		Report errors?

DMN10H120SE-13 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

DMN10H120SE-13 Payment Methods



















DMN10H120SE-13 Shipping Methods













If you have any question about DMN10H120SE-13, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com